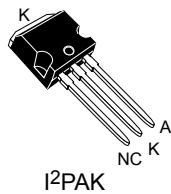
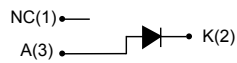



## Automotive 650 V power Schottky silicon carbide diode



### Features

- AEC-Q101 qualified 
- No reverse recovery charge in application current range
- Switching behavior independent of temperature
- Recommended to PFC applications
- PPAP capable
- ECOPACK<sup>®</sup>2 compliant component

### Description

The SiC diode is an ultra-high performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, the STPSC10C065-Y will boost performance in hard switching conditions.

#### Product status link

[STPSC10C065-Y](#)

#### Product summary

$I_{F(AV)}$	10 A
$V_{RRM}$	650 V
$T_j$ (max.)	175 °C

# 1 Characteristics

**Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified)**

Symbol	Parameter		Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage	T <sub>j</sub> from -40 °C to 175 °C	650	V
I <sub>F(RMS)</sub>	Forward rms current		22	A
I <sub>F(AV)</sub>	Average forward current	T <sub>c</sub> = 120 °C, DC current <sup>(1)</sup>	10	A
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms sinusoidal, T <sub>c</sub> = 25 °C	85	A
		t <sub>p</sub> = 10 ms sinusoidal, T <sub>c</sub> = 125 °C	75	
		t <sub>p</sub> = 10 μs square, T <sub>c</sub> = 25 °C	500	
T <sub>stg</sub>	Storage temperature range		-55 to +175	°C
T <sub>j</sub>	Operating junction temperature <sup>(2)</sup>		-40 to +175	°C

1. Value based on R<sub>th(j-c)</sub> max.

2. (dP<sub>tot</sub>/dT<sub>j</sub>) < (1/R<sub>th(j-a)</sub>) condition to avoid thermal runaway for a diode on its own heatsink.

**Table 2. Thermal resistance parameters**

Symbol	Parameter	Value		Unit
		Typ.	Max.	
R <sub>th(j-c)</sub>	Junction to case	1.3	2.0	°C/W

**Table 3. Static electrical characteristics**

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	V <sub>R</sub> = V <sub>RRM</sub>	-	9	100	μA
		T <sub>j</sub> = 150 °C		-	85	425	
V <sub>F</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 10 A	-	1.56	1.75	V
		T <sub>j</sub> = 150 °C		-	1.98	2.50	

1. Pulse test: t<sub>p</sub> = 10 ms, δ < 2%

2. Pulse test: t<sub>p</sub> = 500 μs, δ < 2%

To evaluate the conduction losses, use the following equation:

$$P = 1.35 \times I_{F(AV)} + 0.12 \times I_{F(RMS)}^2$$

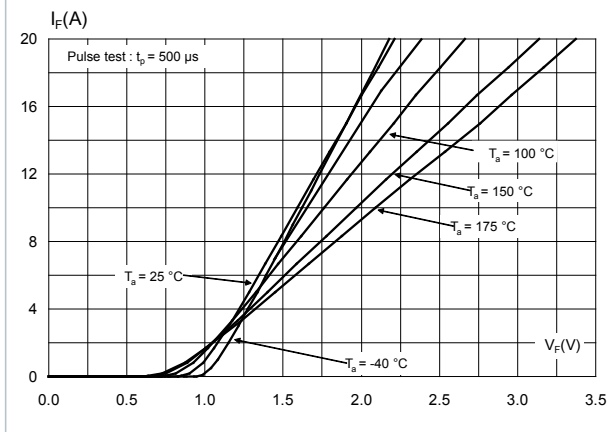
**Table 4. Dynamic electrical characteristics**

Symbol	Parameter	Test conditions	Typ.	Unit
Q <sub>Cj</sub> <sup>(1)</sup>	Total capacitive charge	V <sub>R</sub> = 400 V	26.4	nC
C <sub>j</sub>	Total capacitance	V <sub>R</sub> = 0 V, T <sub>c</sub> = 25 °C, F = 1 MHz	480	pF
		V <sub>R</sub> = 300 V, T <sub>c</sub> = 25 °C, F = 1 MHz	47	

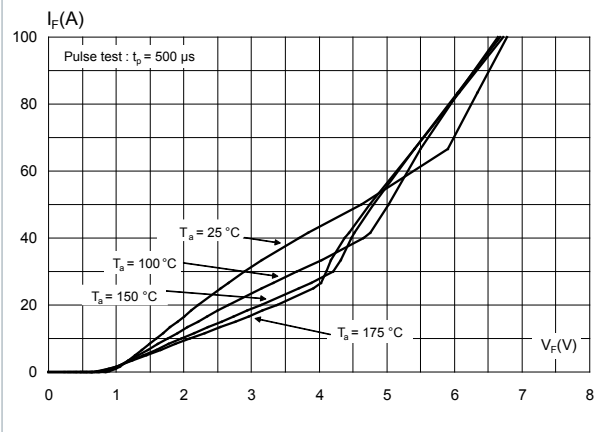
1. Most accurate value for the capacitive charge:  $Q_{Cj}(V_R) = \int_0^{V_R} C_j(V) dV$

## 1.1 Characteristics (curves)

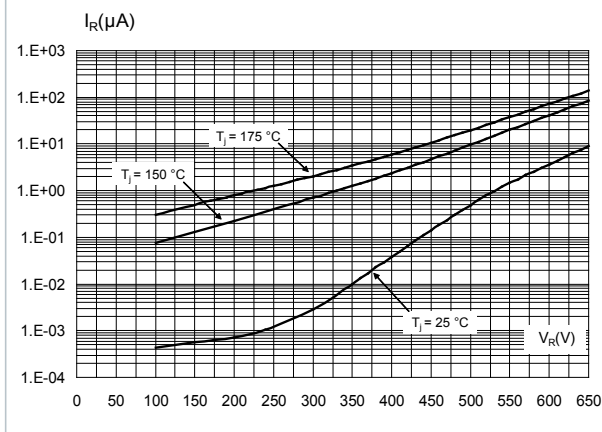
**Figure 1. Forward voltage drop versus forward current (typical values, low level)**



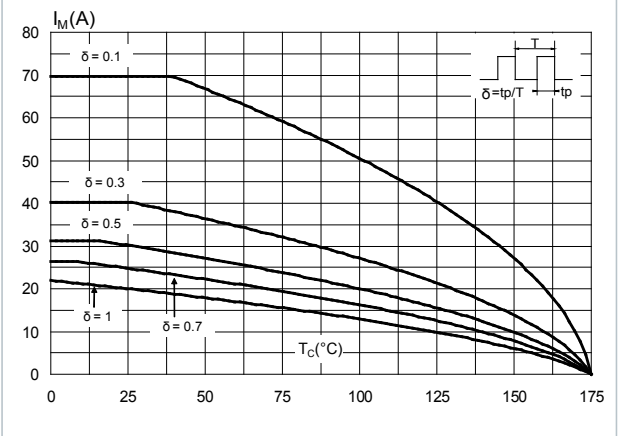
**Figure 2. Forward voltage drop versus forward current (typical values, high level)**



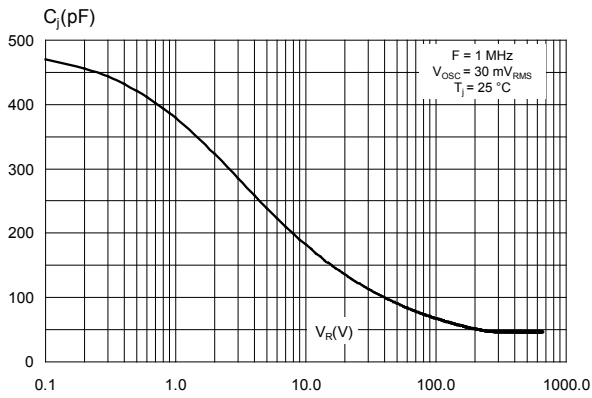
**Figure 3. Reverse leakage current versus reverse voltage applied (typical values)**



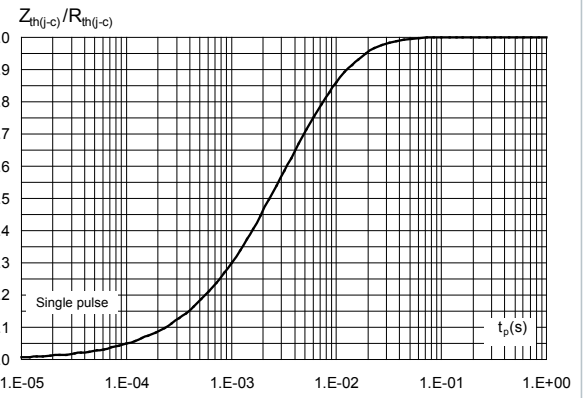
**Figure 4. Peak forward current versus case temperature**



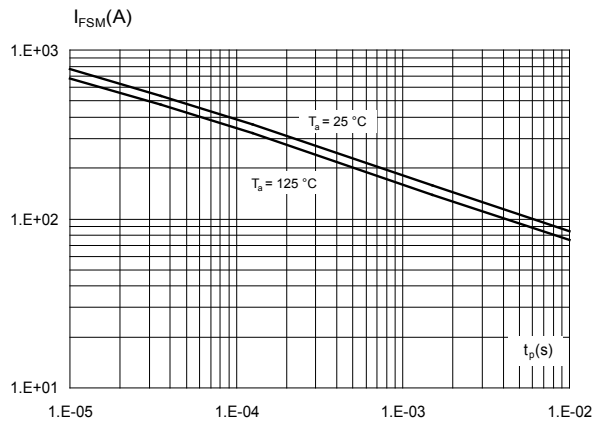
**Figure 5. Junction capacitance versus reverse voltage applied (typical values)**



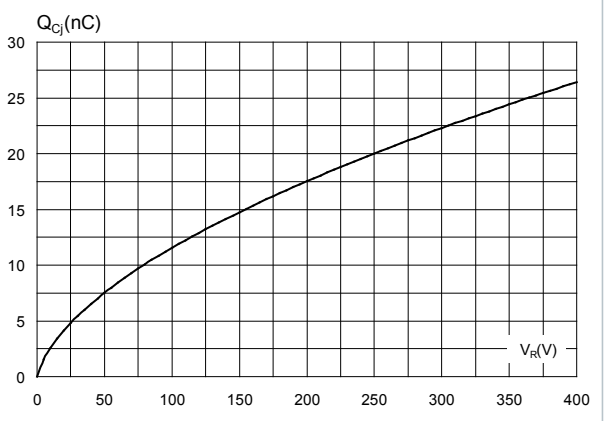
**Figure 6. Relative variation of thermal impedance junction to case versus pulse duration**



**Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)**



**Figure 8. Total capacitive charges versus reverse voltage applied (typical values)**



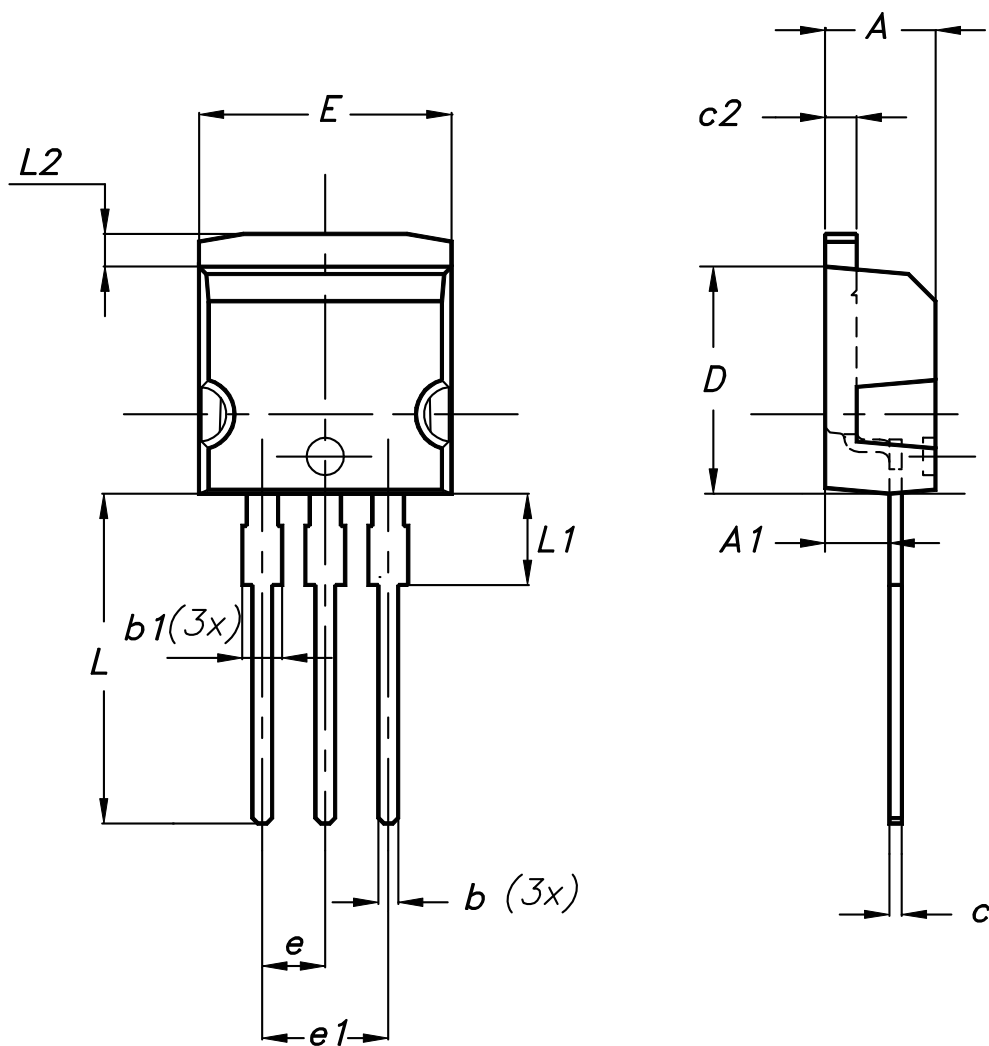
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 2.1 I<sup>2</sup>PAK package information

- Epoxy meets UL 94,V0
- Cooling method: by conduction (C)

Figure 9. I<sup>2</sup>PAK package outline



**Table 5. I<sup>2</sup>PAK package mechanical data**

Ref.	Dimensions			
	Millimeters		Inches (for reference only)	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.40	2.72	0.094	0.107
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.044	0.067
c	0.49	0.70	0.019	0.028
c2	1.23	1.32	0.048	0.052
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
E	10.00	10.40	0.394	0.409
L	13.00	14.00	0.512	0.551
L1	3.50	3.93	0.138	0.155
L2	1.27	1.40	0.050	0.055

### 3 Ordering information

Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC10C065RY	PSC10C065RY	I <sup>2</sup> PAK	1.5 g	50	Tube

## Revision history

**Table 7. Document revision history**

Date	Revision	Changes
16-Feb-2018	1	First issue.
24-Sep-2018	2	Corrected cover image.



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